

## ABSTRACT OF THE DISCLOSURE

The present invention relates to a method of forming a metal feature on an intermediate structure of a semiconductor device that comprises a first exposed metal structure and a second exposed metal structure. The metal feature is selectively formed on the first exposed metal structure without forming on the second exposed metal structure. By adjusting a concentration of stabilizer in an electroless plating solution, the metal feature is electrolessly plated on the first exposed metal structure without plating metal on the second exposed metal structure.

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